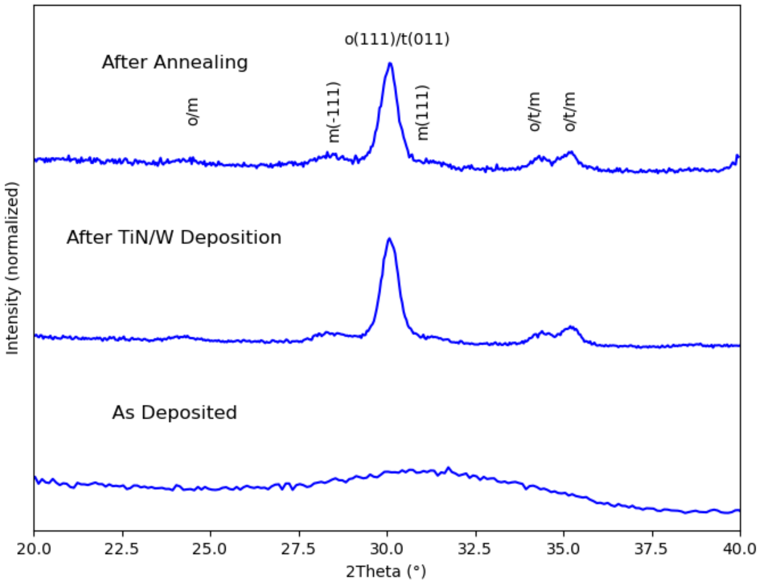

Fig. 1. XRD result for the evolution of the films according to the integration steps: after ALD deposition, after deposition of TiN/W top electrodes by CVD at 380°C and after annealing at 400°C for 1h.

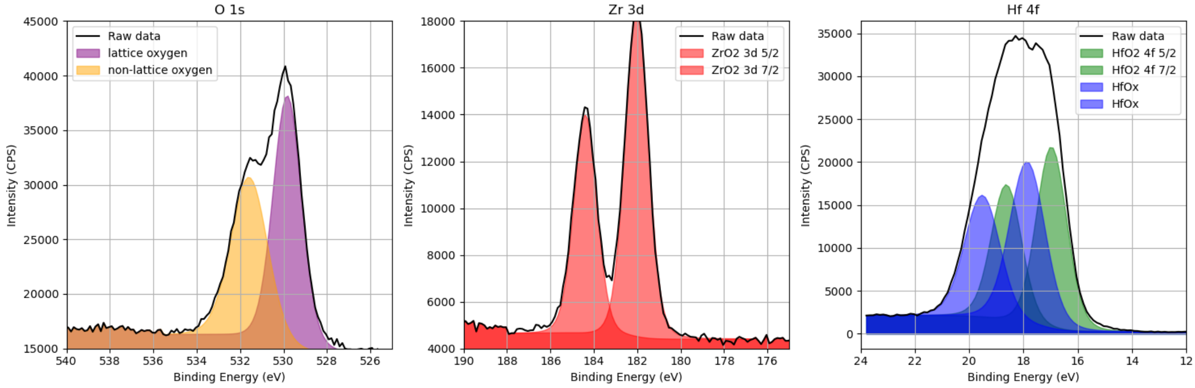

Fig. 2. XPS result after SF_6 plasma etching of top electrode and annealing. The O 1s, Zr 3d and Hf 4f core level of the multilayer sample with a takeoff angle of 45°. Attempt characterization for V_o detection (non-lattice oxygens).

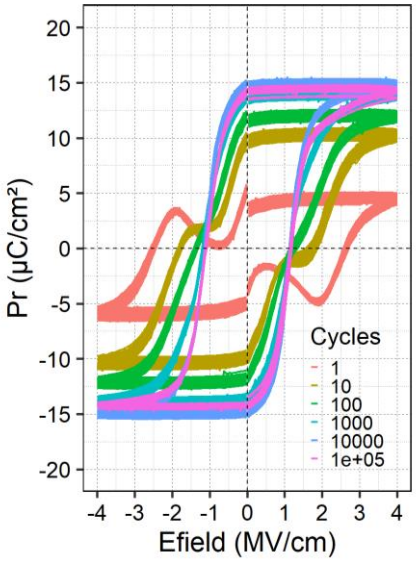

Fig. 3. PUND-corrected P-E measured at 10kHz ±4V HfO_2-ZrO_2 multilayers integrated and annealed capacitors at 400°C for 1h. Cycling has been performed with a 100kHz ±4V triangular signal.

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